4.8 V Bidirectional ESD and **Surge Protection Device**

The NSPM3042 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, high peak pulse current handling capability and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, tablets, MP3 players, digital cameras and many other portable applications where board space comes at a premium.

Features

- Low Clamping Voltage
- Low Leakage
- Small Body Outline: 1.0 mm x 0.6 mm
- Protection for the following IEC Standards:

IEC61000-4-2 Level 4: ±30 kV Contact Discharge IEC61000-4-5 (Lightning) 43 A (8/20 μs)

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Battery Line Protection
- Audio Line Protection
- GPIO

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air	ASK	±30 ±30	kV
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C
Maximum Peak Pulse Current	I _{PP}	43	Α

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1



ON Semiconductor®

www.onsemi.com





MARKING ĎIAGRAM

QM

CASE 714AB

= Specific Device Code

= Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NSPM3042MXT5G	X2DFN2 (Pb-Free)	8000 / Tape & Reel

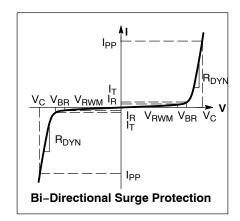
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

	•
Symbol	Parameter
Ipp	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

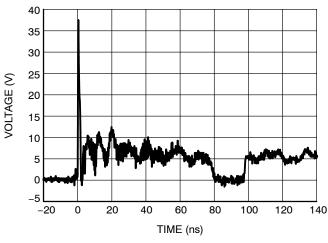
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND Pin 1 to 2 Pin 2 to 1		·C	4.8 4.5	V
Breakdown Voltage	V_{BR}	I _T = 1 mA, I/O Pin to GND Pin 1 to 2 Pin 2 to 1	4.85 4.55	5.2 5.0	6.0 6.0	>
Reverse Leakage Current	I _R	V _{RWM} = 4.8 V, Pin 1 to Pin 2 V _{RWM} = 4.5 V, Pin 2 to Pin 1	MEN		0.5 0.5	μΑ
Clamping Voltage	V _C	IEC61000-4-2, ±8 kV Contact	See	Figures 1	& 2	V
Clamping Voltage TLP (Note 1)	V _C	I _{PP} = 8 A, IEC61000-4-2 Level 2 Equivalent (±4 kV Contact, ± 8 kV Air)	3/1/	5.50		V
		I _{PP} = 16 A, IEC61000-4-2 Level 4 Equivalent (±8 kV Contact, ± 15 kV Air)	W.	5.74		
Reverse Peak Pulse Current	Ipp	IEC61000-4-5 (8 x 20 μs) per Figure 14	43			Α
Clamping Voltage 8x20 µs Waveform per Figure 14 (Note 2)	V _C	Ipp = 1 A Ipp = 43 A		4.9 7.4	6.2 8.0	V
Dynamic Resistance	R _{DYN}	100 ns TLP Pulse		0.03		Ω
Junction Capacitance	670	V _R = 0 V, f = 1 MHz		80	200	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. ANSI/ESD STM5.5.1 Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 1 ns, averaging window: t₁ = 70 ns to t₂ = 90 ns.

2. Non-repetitive current pulse at T_A = 25°C, per IEC61000-4-5 waveform.

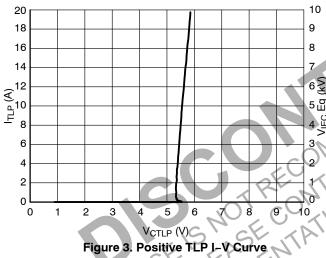
TYPICAL CHARACTERISTICS



0 -10 VOLTAGE (V) -15 -20 -25 -30 -35 -40 60 100 140 -20 0 20 80 120 TIME (ns)

Figure 1. ESD Clamping Voltage Positive 8 kV Contact per IEC61000-4-2

Figure 2. ESD Clamping Voltage Negative 8 kV Contact per IEC61000-4-2



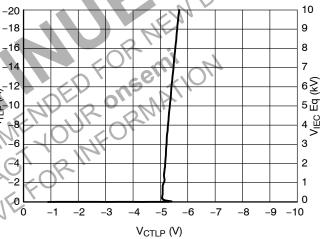
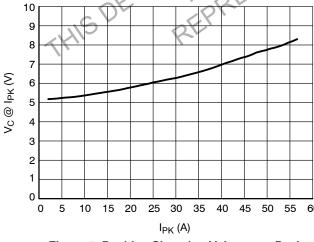


Figure 4. Negative TLP I-V Curve



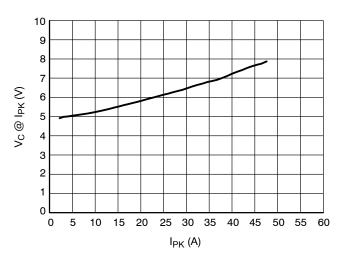


Figure 5. Positive Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20 \mu s$)

Figure 6. Negative Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20 \mu s$)

TYPICAL CHARACTERISTICS

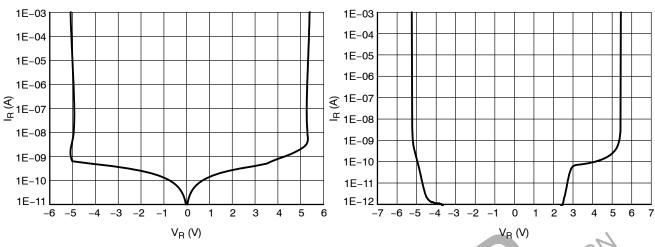
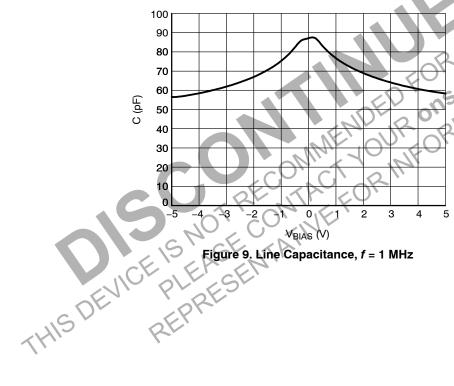


Figure 7. Breakdown Voltage

Figure 8. Reverse Leakage Current



Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I-V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 10. TLP I-V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 11 where an 8 kV IEC 61000-4-2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I-V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels. For more information on TLP measurements and how to interpret them please refer to AND9007/D.

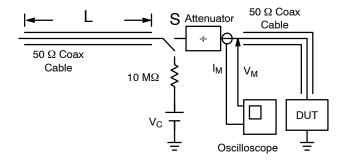
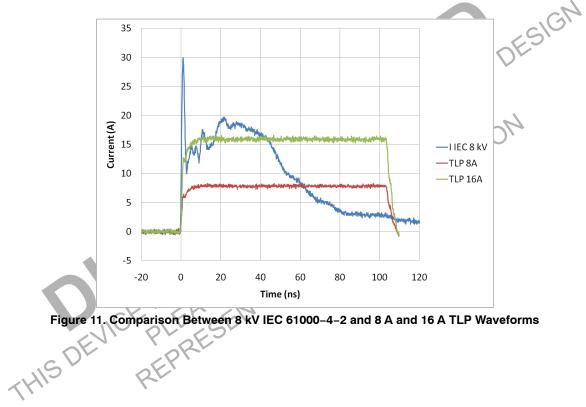


Figure 10. Simplified Schematic of a Typical TLP **System**



IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

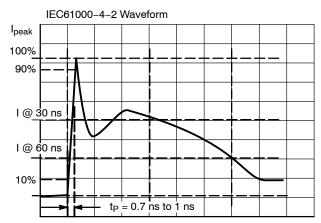


Figure 12. IEC61000-4-2 Spec

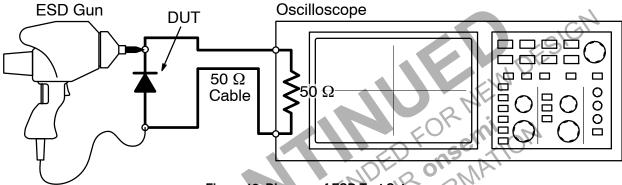


Figure 13. Diagram of ESD Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

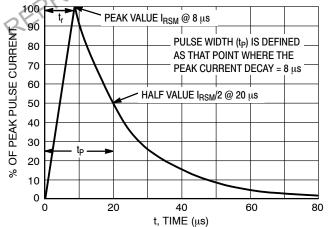


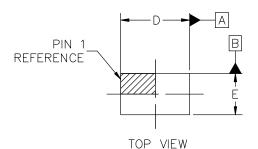
Figure 14. 8 X 20 µs Pulse Waveform

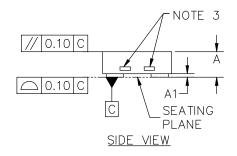


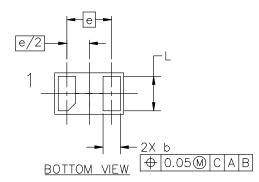


X2DFN2 1.00x0.60x0.37, 0.65PCASE 714AB ISSUE C

DATE 21 FEB 2024



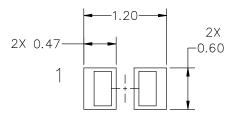




NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- 2. ALL DIMENSION ARE IN MILLIMETERS.
- 3. EXPOSED COPPER ALLOWED AS SHOW.

DIM	MILLIMETERS			
I IVII	MIN.	NOM.	MAX.	
А	0.34	0.37	0.40	
A1		0.03	0.050	
b	0.20	0.25	0.30	
D	0.95	1.00	1.05	
Е	0.55	0.60	0.65	
е	0.65 BSC			
L	0.45	0.50	0.55	



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON98172F	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	X2DFN2 1.00x0.60x0.37, 0.65P		PAGE 1 OF 1	

onsemi and ONSeMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales